

## N-channel 650 V, 0.087 $\Omega$ typ., 32 A MDmesh™ M2 Power MOSFET in a TO-220FP package

Datasheet - production data

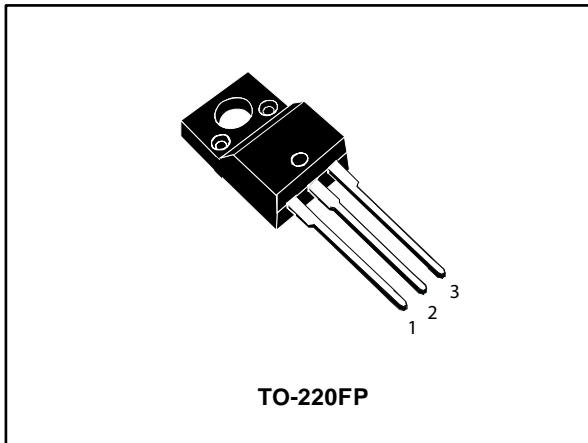
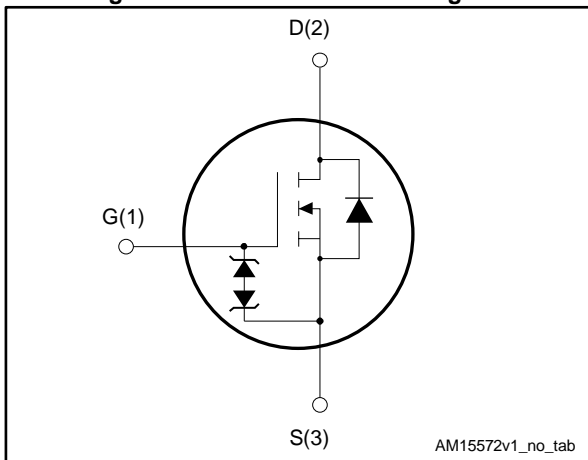


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STF40N65M2	650 V	0.099 $\Omega$	32 A

- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STF40N65M2	40N65M2	TO-220FP	Tube

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	32	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ °C}$	20	A
$I_{DM}^{(2)}$	Drain current (pulsed)	128	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ °C}$ )	2500	V
$T_{stg}$	Storage temperature	- 55 to 150	°C
$T_j$	Max. operating junction temperature	150	

**Notes:**

(1) Limited by maximum junction temperature.

(2) Pulse width limited by safe operating area.

(3)  $I_{SD} \leq 32\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\ peak} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$

(4)  $V_{DS} \leq 520\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	3.13	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.50	°C/W

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	3	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	820	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5: On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage Drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$		0.087	0.099	$\Omega$

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2355	-	pF
$C_{oss}$	Output capacitance		-	102	-	pF
$C_{rss}$	Reverse transfer capacitance		-	2.7	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ V to } 520\text{ V}$ , $V_{GS} = 0\text{ V}$	-	380	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	4.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 32\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15: "Gate charge test circuit"</a> )	-	56.5	-	nC
$Q_{gs}$	Gate-source charge		-	8	-	nC
$Q_{gd}$	Gate-drain charge		-	24	-	nC

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325 \text{ V}$ , $I_D = 16 \text{ A}$ $R_G = 4.7 \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 14: "Switching times test circuit for resistive load"</a> and <a href="#">Figure 19: "Switching time waveform"</a> )	-	15	-	ns
$t_r$	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off-delay time		-	96.5	-	ns
$t_f$	Fall time		-	12	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		32	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		128	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 32 \text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 32 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	468		ns
$Q_{rr}$	Reverse recovery charge		-	8.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	37.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 32 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	610		ns
$Q_{rr}$	Reverse recovery charge		-	11.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	39		A

**Notes:**

<sup>(1)</sup>Pulse width is limited by safe operating area

<sup>(2)</sup>Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.2 Electrical characteristics (curves)

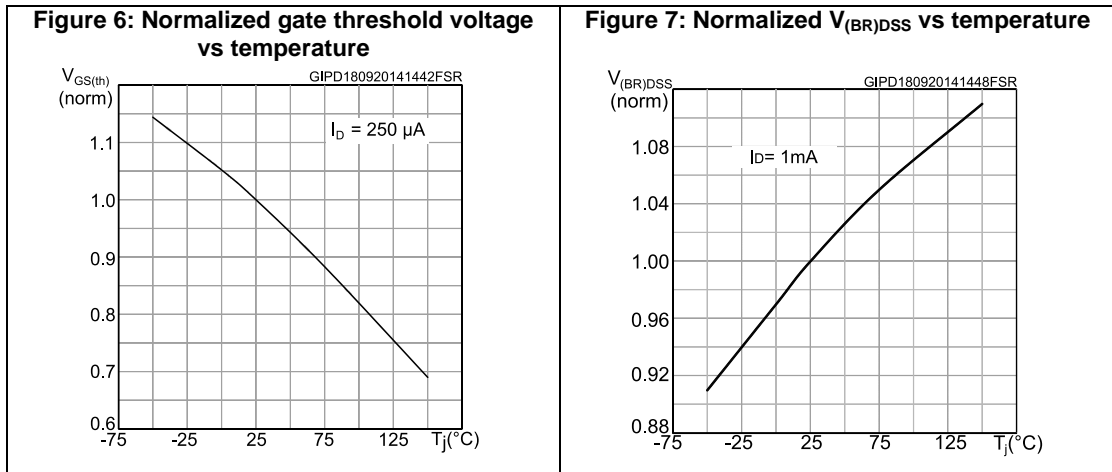
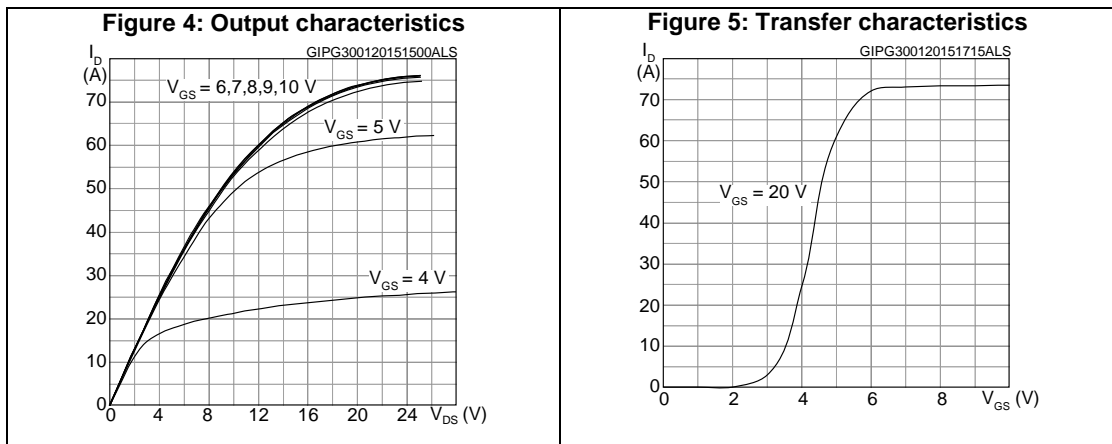
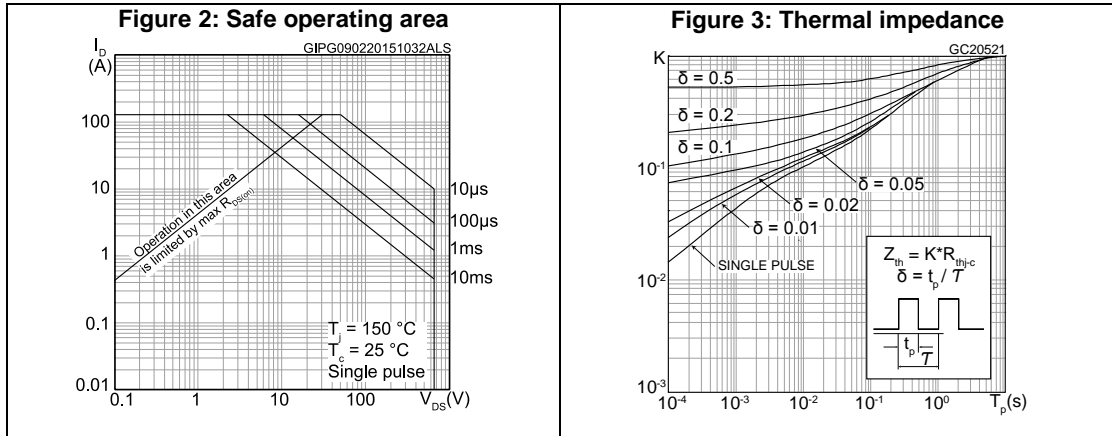


Figure 8: Static drain-source on-resistance

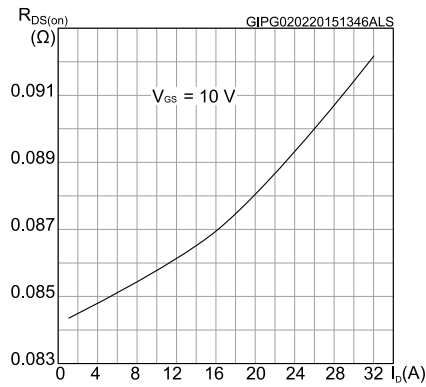


Figure 9: Normalized on-resistance vs. temperature

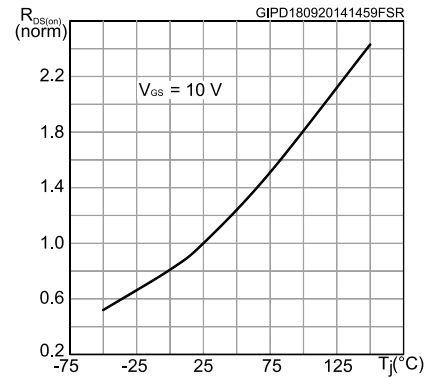


Figure 10: Gate charge vs. gate-source voltage

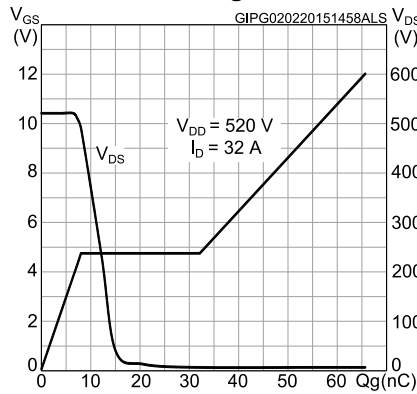


Figure 11: Capacitance variations

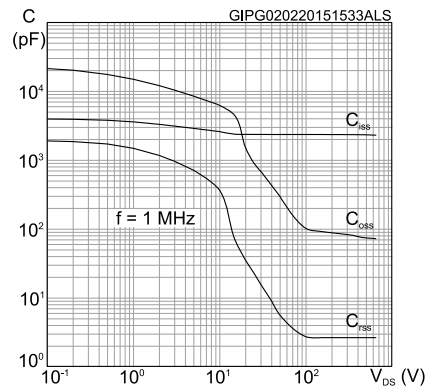


Figure 12: Output capacitance stored energy

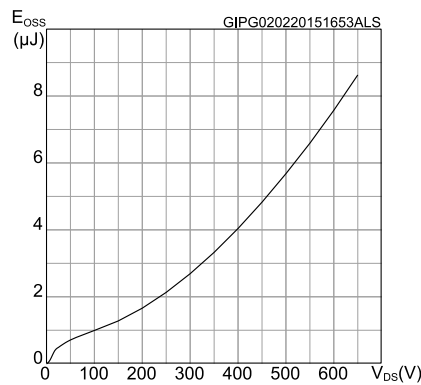
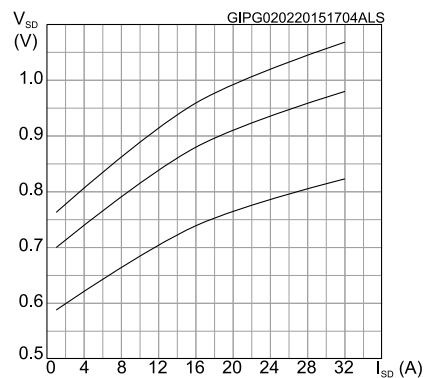
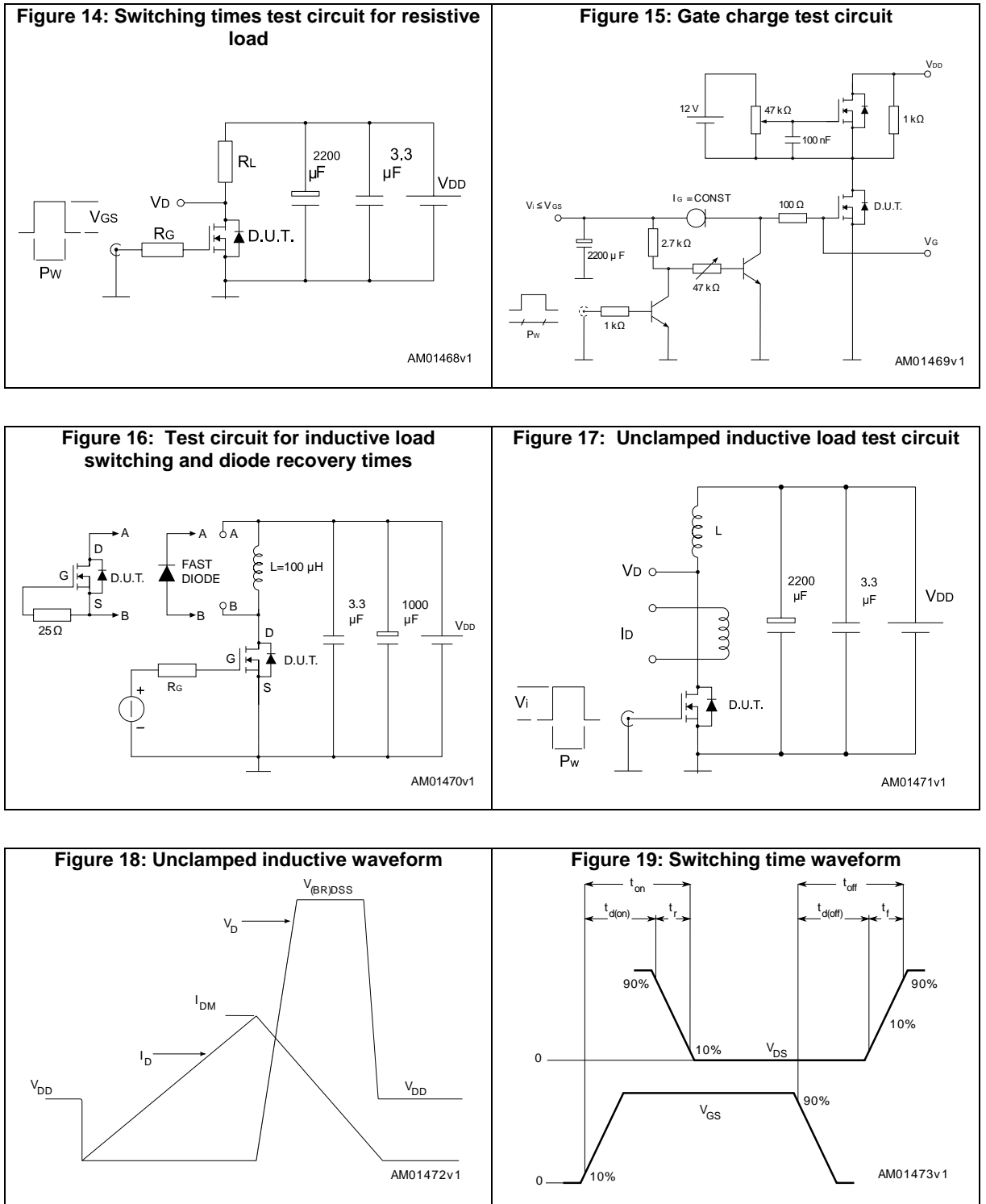


Figure 13: Source-drain diode forward characteristics



### 3 Test circuits



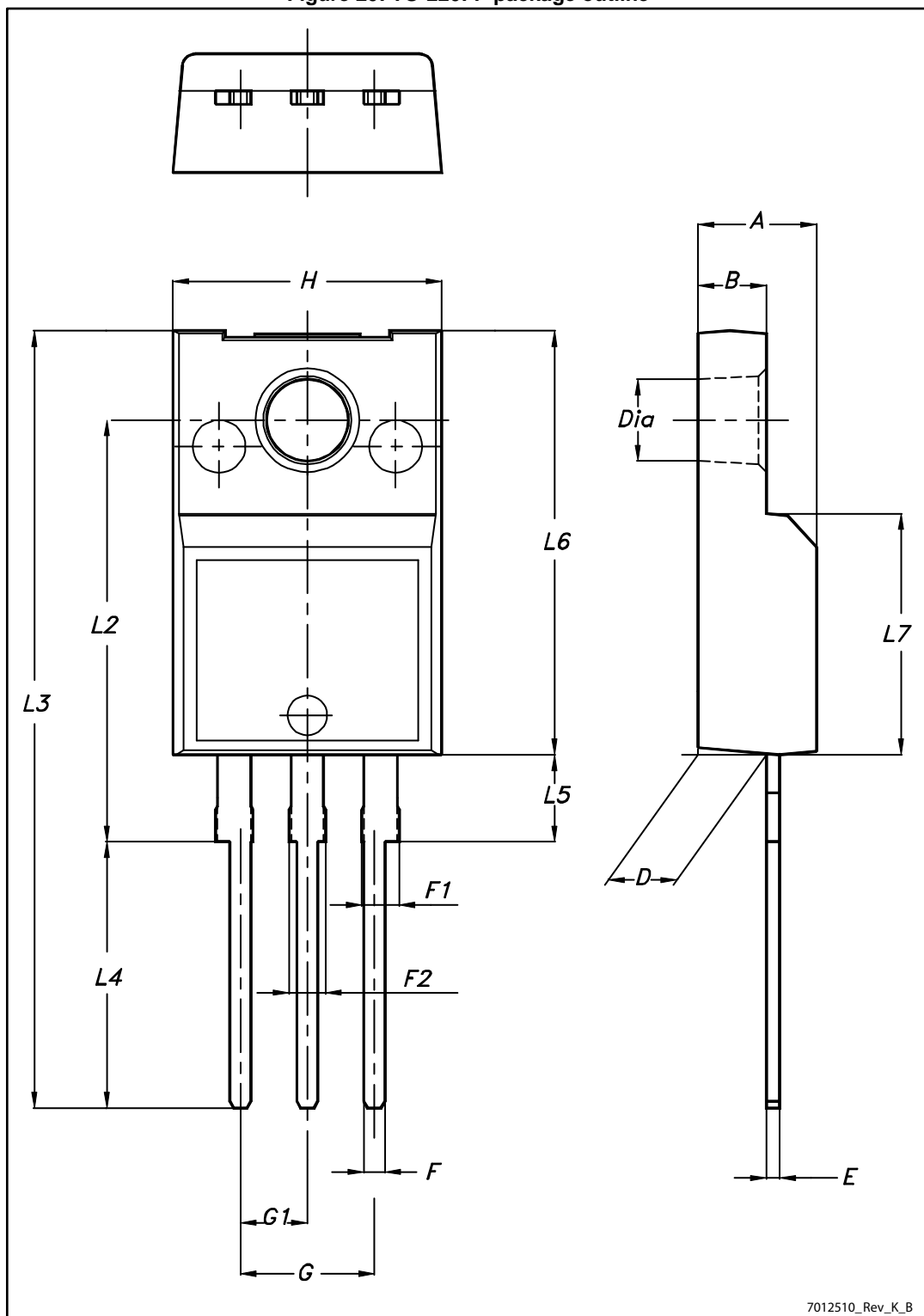


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510\_Rev\_K\_B

Table 9: TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

## 5 Revision history

Table 10: Document revision history

Date	Revision	Changes
09-Feb-2014	1	First release.

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